

# LX5506M

InGaP HBT 4.5 – 6GHz Power Amplifier

#### **PRODUCTION DATA SHEET**

### DESCRIPTION

(U-NII) monolithic microwave chip input matching and output pre- frequency, temperature, and matching. The device is manufactured VSWR. with an InGaP/GaAs Heterojunction positive voltage supply of 3.3V output power in the 4.9-5.9GHz band.

LX5506M features high gain of up to 30dB with low quiescent current of 90mA, and high power added efficiency

The LX5506M is a power amplifier of up to 20% at maximum linear output optimized for the FCC Unlicensed power for OFDM mask compliance. It National Information Infrastructure also features an on-chip output power band, HyperLAN2, and detector to help reduce BOM cost and Japan's WLAN applications in the board space in system implementation. 4.9-5.9 GHz frequency range. The PA The on-chip detector allows simple is implemented as a three-stage interface with an external directional integrated coupler, providing accurate output circuit (MMIC) with active bias, on- power level readings insensitive to load

LX5506M is available in a 16-pin Bipolar Transistor (HBT) IC process 3mmx3mm micro-lead package (MLP). (MOCVD). It operates with a single The compact footprint, low profile, and excellent thermal capability of the MLP (nominal), with up to +22dBm linear package makes the LX5506M an ideal output power for 802.11a OFDM solution for broadband, high-gain spectrum mask compliance, and low power amplifier requirements for IEEE EVM of -30dB for up to +18dBm 802.11a, and HyperLAN2 portable WLAN applications.

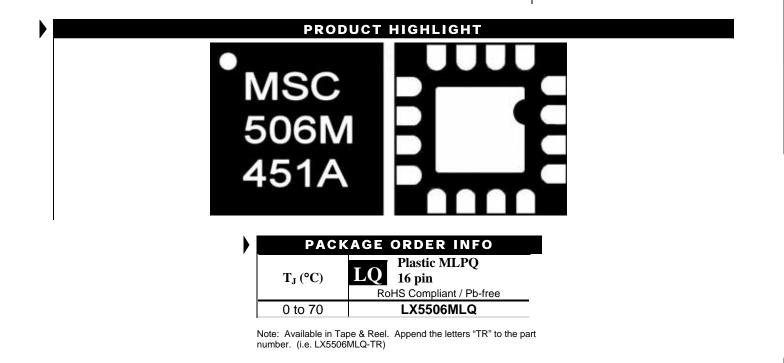
IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

#### **KEY FEATURES**

- . Broadband 4.9-5.9GHz Operation
- Advanced InGaP HBT
- Single-Polarity 3.3V Supply
- Power Gain ~ 30dB at 5.25GHz
- Power Gain > ~28dB Across 4.9-5.9GHz
- EVM ~ -30dB at Pout=+17dBm at 5.25GHz
- EVM ~ -30dB at Pout=+18dBm at 5.85GHz
- Total Current ~140mA for Pout = +17dBm at 5.25GHz (For High Duty Cycle of 90%)
- Maximum Linear Power ~ +22dBm for OFDM Mask Compliance
- Maximum Linear Efficiency ~ 20%
- On-chip Output Power Detector with Improved Frequency and Load-VSWR Insensitivity
- **On-Chip Input Match**
- On-Chip RF Decoupling Simple Output Match for Optimal Broadband EVM
- Small Footprint: 3x3mm<sup>2</sup>
- Low Profile: 0.9mm

#### APPLICATIONS

- FCC U-NII Wireless
- . IEEE 802.11a
- HyperLAN2
- 5GHz Cordless Phone





## INFORMATION

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We look forward to hearing from you.